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## **NTE5587, NTE5589, NTE5593 Silicon Controlled Rectifier (SCR) 550 Amp, TO118**

### **Features:**

- Low On-State Voltage
- High di/dt
- High dv/dt
- Excellent Surge and I<sup>2</sup>t Ratings

### **Applications:**

- Power Supplies
- Battery Chargers
- Motor Controls

### **Absolute Maximum Ratings and Electrical Characteristics:**

Repetitive Peak Voltages, V<sub>DRM</sub> & V<sub>RRM</sub>

NTE5587 .....	600V
NTE5589 .....	1200V
NTE5593 .....	1600V

RMS On-State Current, I<sub>T(RMS)</sub> .....

550A

Average On-State Current, I<sub>T(AV)</sub> .....

350A

Peak One-Cycle, Non-Repetitive On-State Surge Current, I<sub>TSM</sub>

50Hz .....

9100A

60Hz .....

10,000A

Critical Rate-of-Rise of On-State Current, di/dt

Repetitive .....

150A/ s

Non-Repetitive .....

800A/ s

I<sup>2</sup>t for Fusing (8.2ms), I<sup>2</sup>t .....

416,000A<sup>2</sup>sec

Peak Gate Power Dissipation, P<sub>GM</sub> .....

16W

Average Gate Power Dissipation, P<sub>G(AV)</sub> .....

3W

Peak On-State Voltage (I<sub>TM</sub> = 625A, T<sub>J</sub> = +25°C), V<sub>TM</sub> .....

1.4V

Peak Forward Leakage Current (At V<sub>DRM</sub>, T<sub>J</sub> = +125°C), I<sub>DRM</sub> .....

30mA

Peak Reverse Leakage Current (At V<sub>RRM</sub>, T<sub>J</sub> = +125°C), I<sub>RRM</sub> .....

30mA

Gate Current to Trigger (V<sub>D</sub> = 12V, T<sub>J</sub> = +25°C), I<sub>GT</sub> .....

150mA

Gate Voltage to Trigger (V<sub>D</sub> = 12V, T<sub>J</sub> = +25°C), V<sub>GT</sub> .....

3V

Non-Triggering Gate Voltage (At V<sub>DRM</sub>, T<sub>J</sub> = +125°C), V<sub>GDM</sub> .....

0.15V

## Absolute Maximum Ratings and Electrical Characteristics (Cont'd):

Peak Forward Gate Current, $I_{GTM}$	.....	4A
Peak Reverse Gate Voltage, $V_{GRM}$	.....	5V
Typical Turn-Off Time, $t_{q}$ ( $I_T = 250A$ , $di_R/dt = 25A/\text{s}$ , re-applied, $dv/dt = 20V/\text{s}$ , linear to $0.8V_{DRM}$ , $T_J = +125^\circ\text{C}$ )	150 s	
Typical Turn-On Time ( $V_D = 100V$ , $I_T = 100A$ ), $t_{on}$	.....	7 s
Minimum Critical $dv/dt$ exponential to $V_{DRM}$ ( $T_J = +125^\circ\text{C}$ ), $dv/dt$	.....	300V/s
Operating Junction Temperature Range, $T_J$	.....	-40° to +125°C
Storage Temperature Range, $T_{stg}$	.....	-40° to +150°C
Maximum Thermal Resistance, Junction-to-Case, $R_{thJC}$	.....	0.10°C/W
Maximum Thermal Resistance, Case-to-Sink (Lubricated), $R_{thCS}$	.....	0.05°C/W
Mounting Torque	.....	360in.-lb.
Mounting Torque (Lubricated)	.....	400kg-cm

